

Product Summary

BV _{DSS}	R _{DS(on)} max	I _D max T _A = 25°C
100V	3.0Ω @ V _{GS} = 10V	0.6A
	4.5Ω @ V _{GS} = 5.0V	0.5A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC converters
- Power management functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

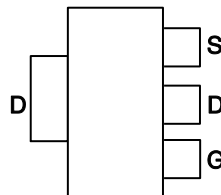
Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.112 grams (Approximate)

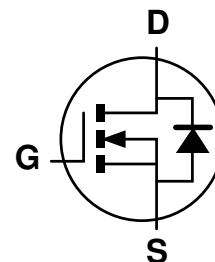
SOT223 (Type DN)



Top View



Pin Out - Top View



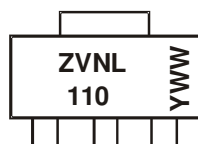
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
ZVNL110GTA	SOT223 (Type DN)	1,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



ZVNL110 = Product Type Marking Code
 YWW = Date Code Marking
 Y or Ȳ = Last Digit of Year (ex: 2= 2022)
 WW or WW = Week Code (01~53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	0.6	A
		$T_A = +70^\circ\text{C}$		0.5	
Pulsed Drain Current (10 μs Pulse, Duty Cycle $\leq 1\%$)			I_{DM}	6	A
Maximum Body Diode Continuous Current (Note 6)			I_S	0.6	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	1.1	W
	(Note 6)		2.0	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	113	$^\circ\text{C/W}$
	(Note 6)		61	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	6.6	$^\circ\text{C}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	10 100	μA	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 80\text{V}, V_{GS} = 0\text{V}, T_J = +125^\circ\text{C}$
Gate-Body Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
On-State Drain Current	$I_{D(on)}$	750	—	—	mA	$V_{DS} = 25\text{V}, V_{GS} = 5\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.75	—	1.5	V	$V_{DS} = V_{GS}, I_D = 1\text{mA}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	3.0	Ω	$V_{GS} = 10\text{V}, I_D = 500\text{mA}$
		—	—	4.5		$V_{GS} = 5.0\text{V}, I_D = 250\text{mA}$
Forward Transconductance	g_{fs}	225	—	—	mS	$V_{DS} = 25\text{V}, I_D = 500\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	47	75	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	23	25		
Reverse Transfer Capacitance	C_{rss}	—	6	8		
Turn-On Delay Time	$t_{D(on)}$	—	2	7	ns	$V_{DD} = 25\text{V}, V_{GS} = 10\text{V},$ $R_G = 6.0\Omega, I_D = 1.0\text{A}$
Turn-On Rise Time	t_R	—	3	12		
Turn-Off Delay Time	$t_{D(off)}$	—	5	15		
Turn-Off Fall Time	t_F	—	2	13		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

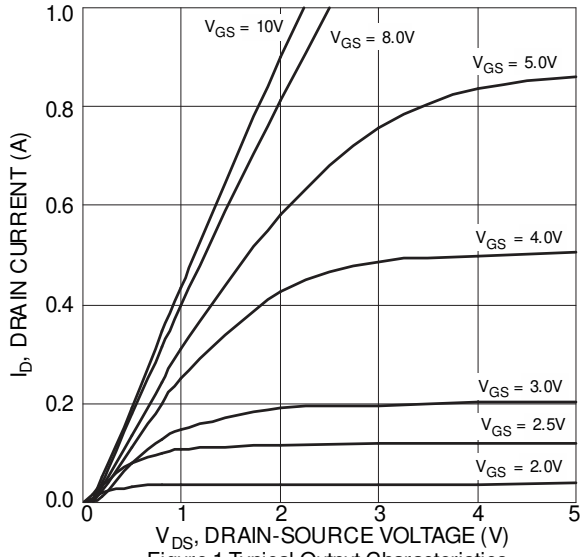


Figure 1 Typical Output Characteristics

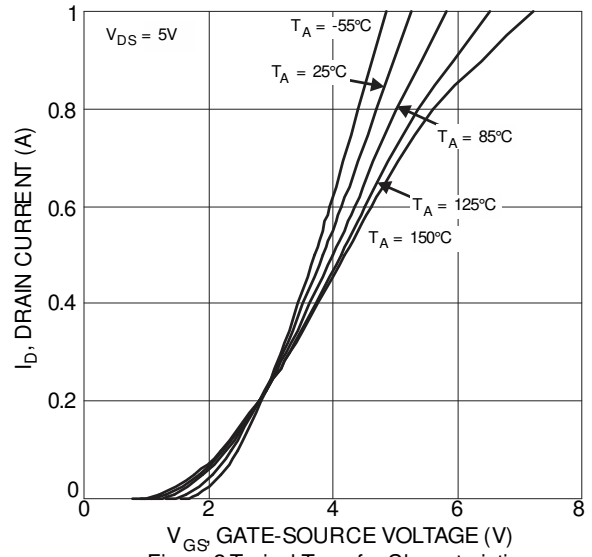


Figure 2 Typical Transfer Characteristics

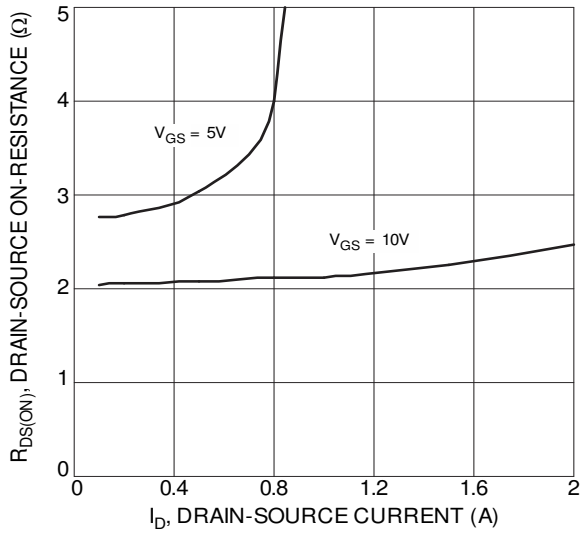


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

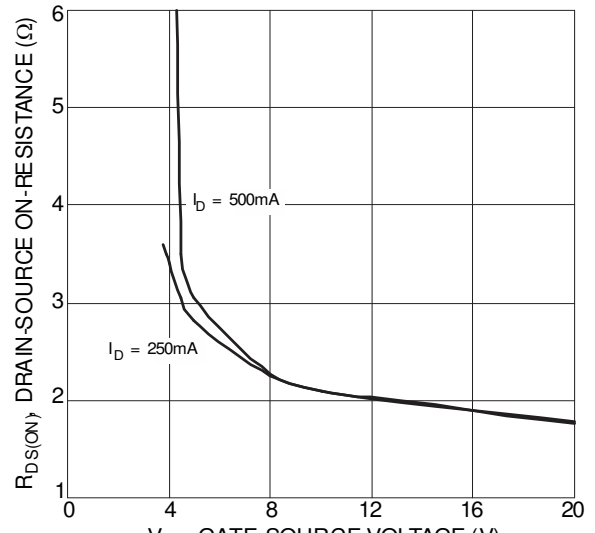


Figure 4 Typical Transfer Characteristics

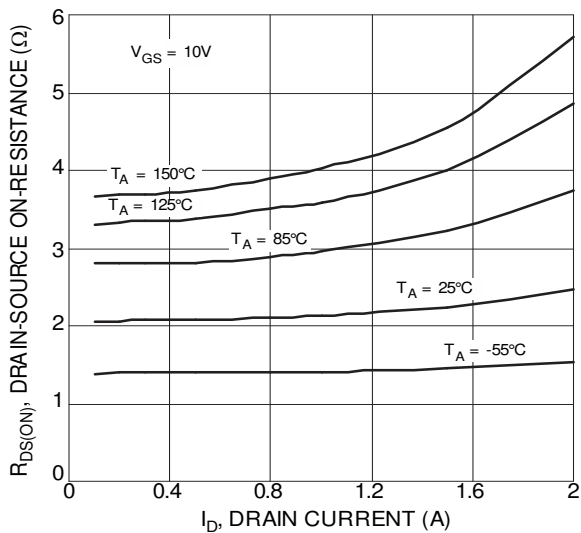


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

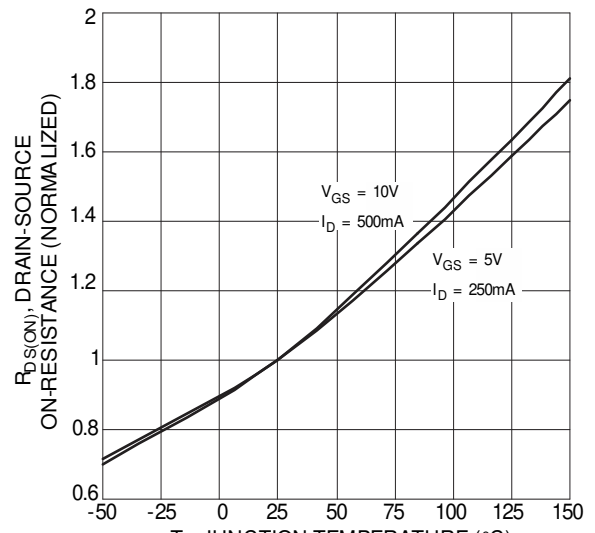


Figure 6 On-Resistance Variation with Temperature

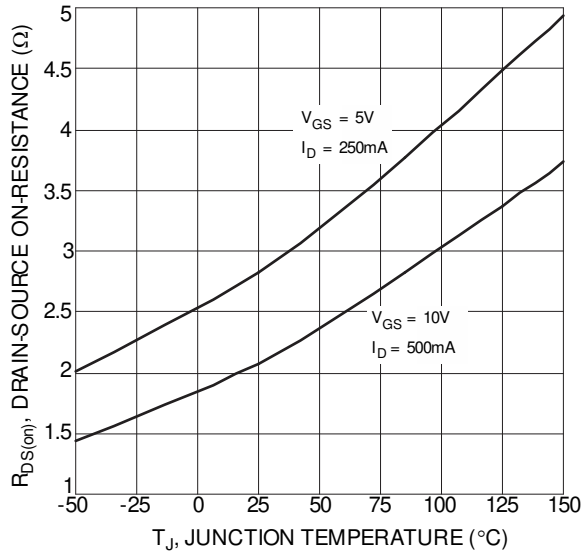


Figure 7 On-Resistance Variation with Temperature

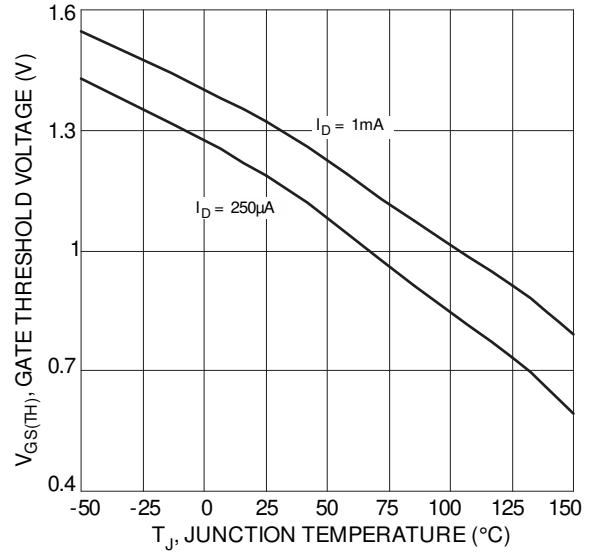


Figure 8 Gate Threshold Variation vs. Temperature

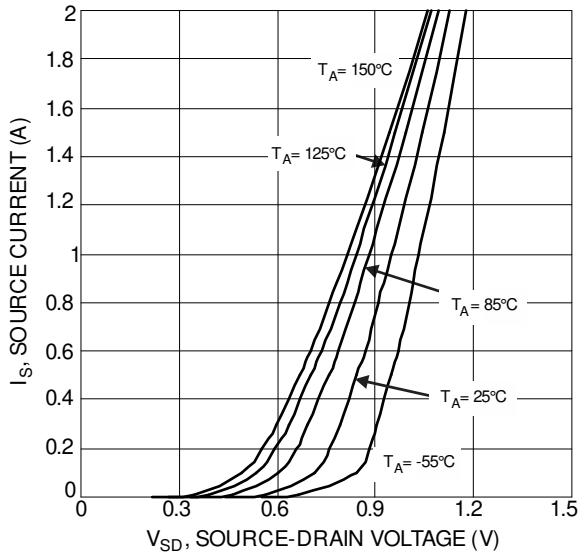


Figure 9 Diode Forward Voltage vs. Current

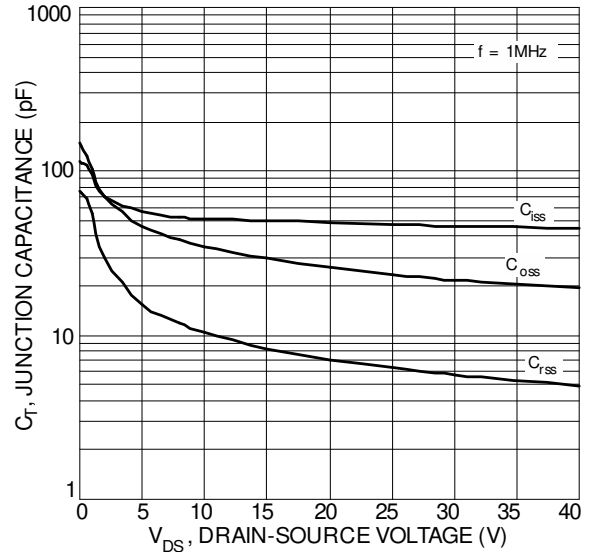


Figure 10 Typical Junction Capacitance

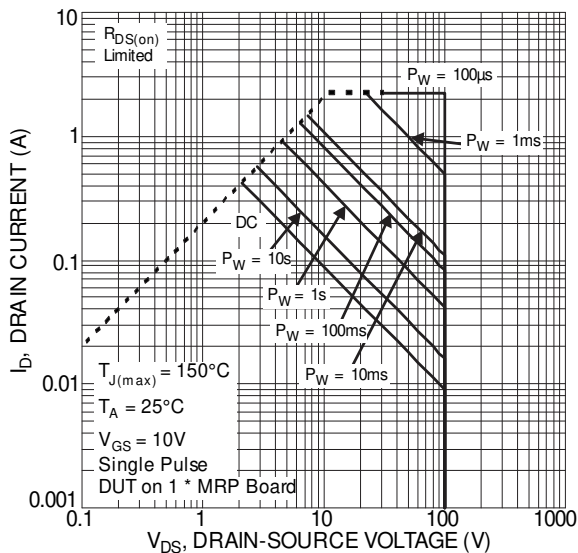
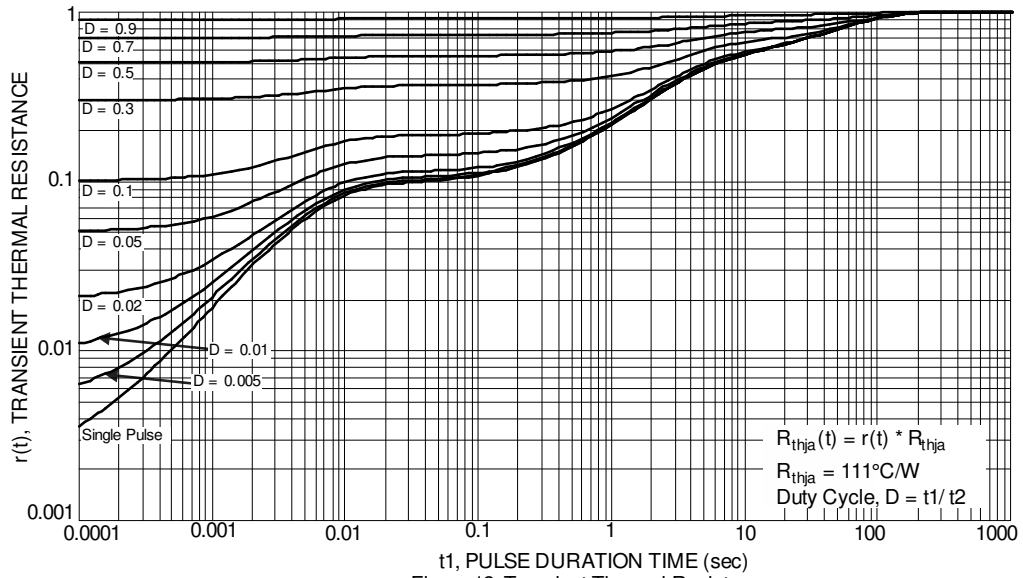


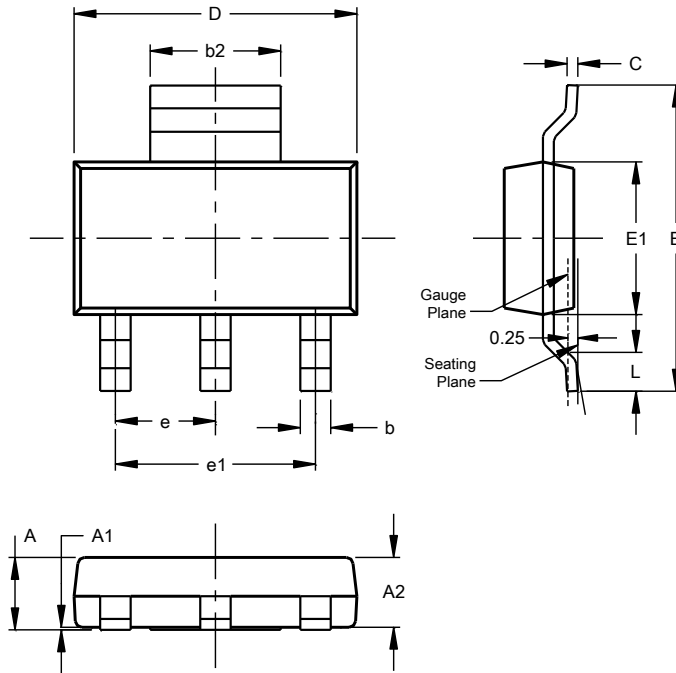
Figure 11 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

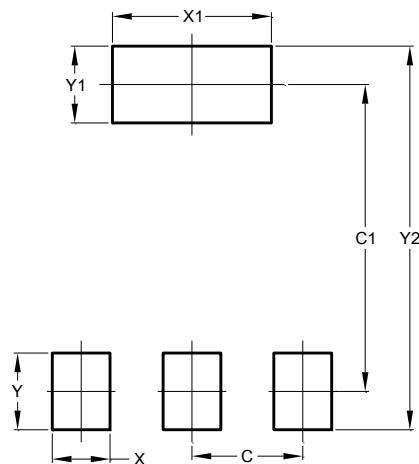


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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